TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM3K04FS

## High Speed Switch Applications

Unit: mm

- With built-in gate-source resistor:  $RGS = 1 M\Omega$  (typ.)
- 2.5 V gate drive
- Low gate threshold voltage:  $V_{th} = 0.7 \sim 1.3 \text{ V}$
- Small package

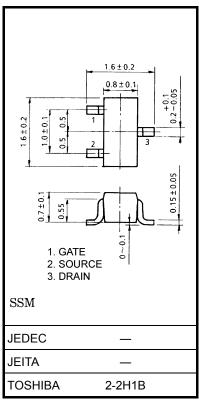
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## **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DS}$	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
DC drain current	ID	100	mA
Drain power dissipation	P <sub>D</sub>	100	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the



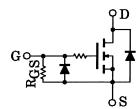
Weight: 2.4 mg (typ.)

Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Marking



#### **Equivalent Circuit**





# **Electrical Characteristics (Ta = 25°C)**

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0	_	_	15	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0	_	_	1	μА
Gate threshold vo	Itage	V <sub>th</sub>	$V_{DS} = 3 \text{ V}, I_{D} = 0.1 \text{ mA}$	0.7	_	1.3	V
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$	25	50	_	mS
Drain-source ON resistance		R <sub>DS</sub> (ON)	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	4	12	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	11.0	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.3	_	pF
Output capacitance		Coss	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	9.3	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$	_	0.16	_	μS
	Turn-off time	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$	_	0.19	_	
Gate-source resistor		R <sub>GS</sub>	V <sub>GS</sub> = 0~10 V	0.7	1.0	1.3	МΩ

# **Switching Time Test Circuit**

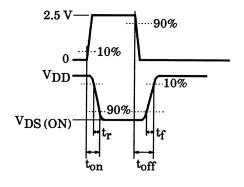
(a) Test circuit

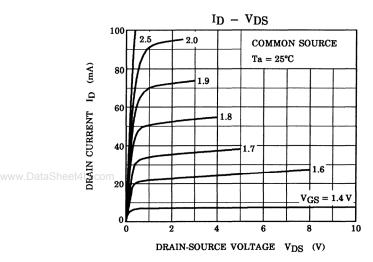
OUT  $V_{DD} = 3 V$ D.U.  $\leq 1\%$   $V_{IN} : t_r, t_f < 5 \text{ ns}$   $(Z_{out} = 50 \Omega)$ COMMON SOURCE

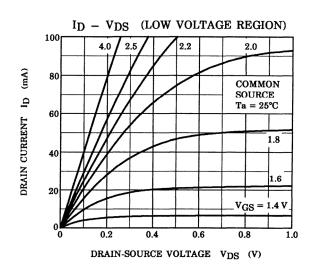
 $Ta = 25^{\circ}C$ 

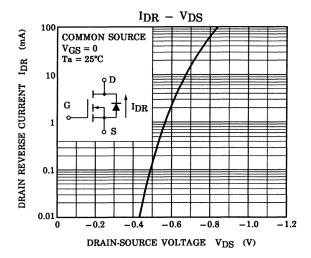
(b) V<sub>IN</sub> V<sub>GS</sub>

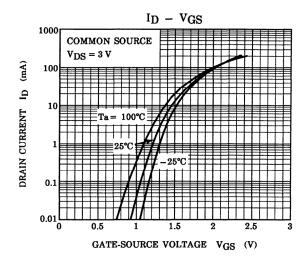
(c) V<sub>OUT</sub> V<sub>DS</sub>

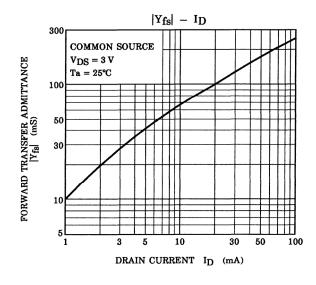


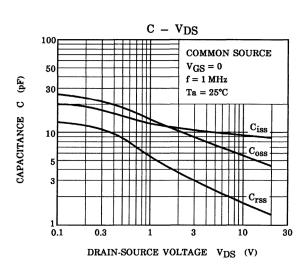


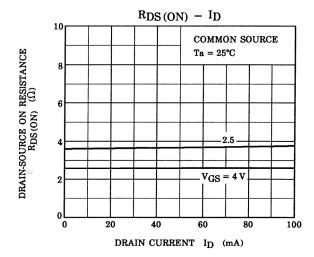


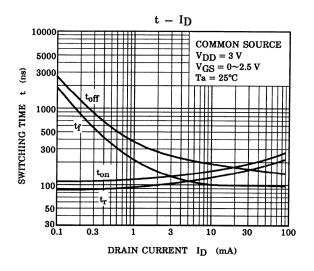


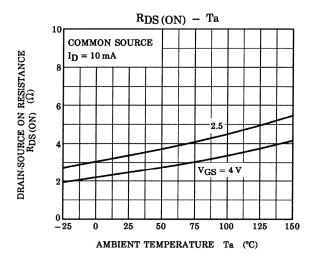


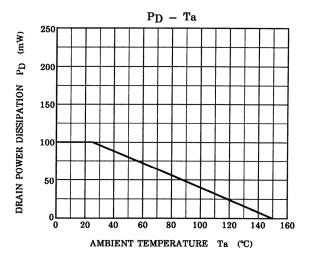












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